

Impact of Metal-Pad Placement on Waveguide Loss and Modulation Performance in Graphene-Integrated SiN Ring Modulator

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Chip-scale electro-absorption graphene ring modulators can outperform straight-geometry modulators in terms of modulation depth and speed. However, their design is more complex, demanding precise control of parameters such as bus-ring coupling efficiency, resonator circumference, and waveguide loss, all of which strongly influence the device's resonance [1,2]. Additionally, metallic contacts for biasing graphene can cause parasitic propagation loss in the waveguide affecting the critical coupling and output bus transmission of the modulator. Here, we systematically investigate metal-pad placement in graphene-based electro-absorption modulators integrated with silicon nitride (SiN) ring resonators, focusing on how the pad-waveguide gap affects waveguide excess loss. Finite-difference time-domain (FDTD) simulations reveal that these excess losses—beyond intrinsic propagation loss—drop exponentially with increasing pad-to-waveguide distance. For a 10 μm graphene region on an 80 μm ring circumference, lowering the additional loss from 1 dB to 0 dB improves the modulation depth from -15 dB to -35 dB. This underscores the critical role of precise metallization in optimizing optical confinement and graphene-light interaction, offering a route to higher modulation depths and potentially faster operating speeds in compact, energy-efficient photonic integrated circuits.

References

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- [2] B. Little, S. Chu, H. A. Haus, J. Foresi, and J.-P. Laine, *J. Lightwave Technol.*, 15 (1997), 998-1005

Figures

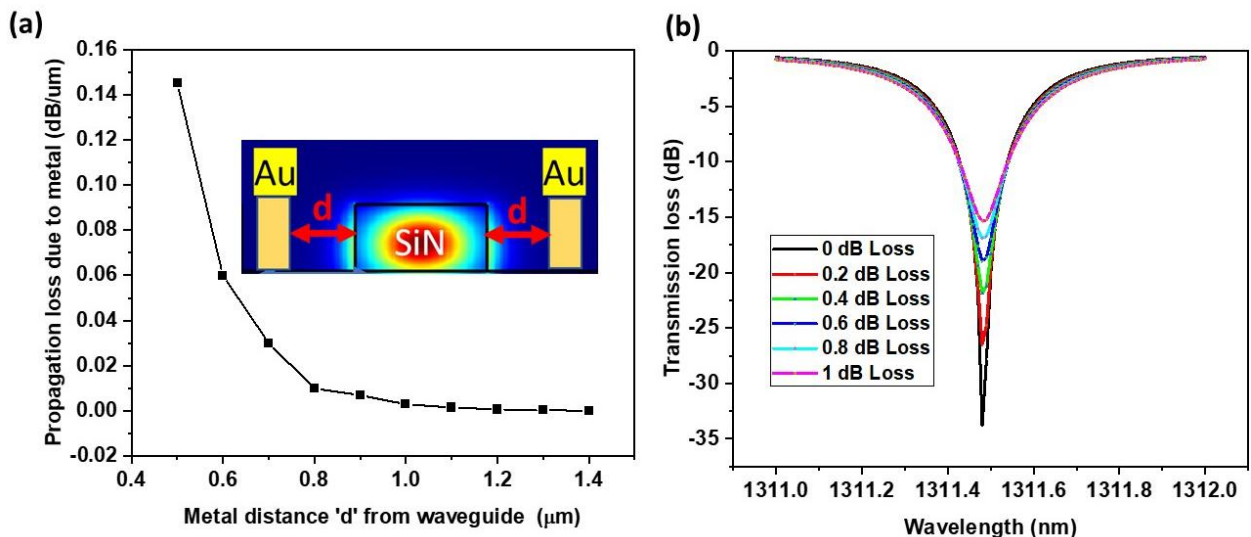


Figure 1: (a) Loss vs. metal distance, with insets showing the TE mode propagation in the waveguide. (b) Transmission loss for different metal-induced excess losses.

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